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Appl. No. 10/605,499  
Amdt. dated January 24, 2006  
Reply to Office action of November 02, 2005

hole;

performing a fifth ~~photo-etching process~~ photo-etching process to form a source wire and a drain wire on the first isolation layer, the source wire and the drain wire being electrically connected to the source electrode and the drain electrode through the first contact hole respectively; and  
forming a second isolation layer over the substrate to cover the first isolation layer, the source wire, and the drain wire.

2. (Original) The method of claim 1 wherein the substrate comprises a glass substrate or a quartz substrate.

3. (Original) The method of claim 1 wherein the method for forming the polysilicon layer further comprises the following steps:  
performing a sputtering process to form an amorphous silicon layer on the surface of the substrate; and  
performing an annealing process to re-crystallize the amorphous silicon layer to the polysilicon layer.

4. (Original) The method of claim 3 wherein the annealing process is an excimer laser annealing process.

5. (Original) The method of claim 1 wherein the P-type ion implantation process is a high concentration P-type ion implantation process to form the source electrode and the drain electrode.

6. (Currently amended) The method of claim 1 wherein a step for forming a third isolation layer over the entire substrate is performed before the second ~~photo-etching process~~ photo-etching process to cover the active area and the

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bottom storage electrode.

7. (Current amended) The method of claim 6 wherein the material composition of the third isolation layer comprises ~~silicon oxide formed by utilizing~~  
5 ~~tetra-ethyl-ortho-silicate(TEOS) as a reaction gas, silicon oxide, or silicon nitride~~  
silicon oxide, silicon nitride, or silicon oxide which is formed by utilizing  
tetra-ethyl-ortho-silicate as a reaction gas.
8. (Original) The method of claim 1 wherein a step for forming a fourth isolation layer on  
10 the entire substrate is performed after removing the first mask to cover the active  
area and the bottom storage electrode.
9. (Currently amended) The method of claim 8 wherein the material composition of the  
15 ~~fourth isolation layer comprises silicon oxide formed by utilizing~~  
~~tetra-ethyl-ortho-silicate(TEOS) as a reaction gas, silicon oxide, or silicon nitride~~  
silicon oxide, silicon nitride, or silicon oxide which is formed by utilizing  
tetra-ethyl-ortho-silicate as a reaction gas.
10. (Original) The method of claim 1 wherein the material composition of the metal layer  
20 comprises tungsten (W) or chrome (Cr).
11. (Original) The method of claim 1 wherein the first isolation layer comprises a silicon  
oxide layer, a silicon nitride layer, or a silicon oxynitride layer.
- 25 12. (Original) The method of claim 1 wherein the source wire is used as a data line.
13. (Currently amended) The method of claim 1 wherein the second isolation layer is a  
planarization layer, and the second isolation layer comprises -a silicon- oxide layer, a

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silicon nitride layer, or a silicon oxide layer formed by utilizing  
tetra-ethyl-ortho-silicate as a reaction gas.

14. (Original) The method of claim 1 wherein the material composition of the transparent  
5       conductive layer comprises indium tin oxide (ITO) or indium zinc oxide (IZO).
15. (Currently amended) The method of claim 1 further comprising the following steps:  
performing a sixth ~~photo-etching process~~ photo-etching process to remove portions  
of the second isolation layer to form at least one second contact hole electrically  
10       connected to the drain wire;  
forming a transparent conductive layer on the second isolation layer; and  
performing a seventh ~~photo-etching process~~ photo-etching process to remove  
portions of the transparent conductive layer to form at least one pixel electrode on  
the second isolation layer, each pixel electrode being electrically connected to  
15       each drain wire through each second contact hole filled with the transparent  
conductive layer.